SiGe, Ge, and Related Compounds 5: Materials, Processing, and Devices

Editors:

D. Harame
IBM, Systems and Technology Group
Essex Junction, Vermont, USA

T. Krishnamohan
Intel Corporation
Santa Clara, California, USA

S. Miyazaki
Nagoya University
Nagoya, Japan

A. Reznicek
IBM, T.J. Watson Research Center
Yorktown Heights, New York, USA

B. Tillack
IHP
Frankfurt (Oder), Germany
and
TU Berlin
Berlin, Germany

Y. C. Yeo
The National University of Singapore
Singapore

M. Caymax
imec
Leuven, Belgium

G. Masini
Luxtera
Carlsbad, California, USA

G. Niu
Auburn University
Auburn, Alabama, USA

K. Saraswat
Stanford University
Palo Alto, California, USA

B. Vincent
imec
Leuven, Belgium

K. Uchida
Keio University
Yokohama, Japan

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9:00 to 9:30 PM
Speakers
T. Ning (IBM), S. Takaga (University of Tokyo), W. Maszara (Global Foundries), C. Claeys (imec), K. Uchida (Keio University), P. Gargini (Intel)

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R. Loo, B. Vincent, F. Gencarelli, C. Merckling, A. Kumar, G. Eneman, L. Witters, W. Vandervorst, M. Caymax, M. Heyns, and A. Thean (imec)

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G. Grzybowski, R. T. Beeler, L. Jiang, D. J. Smith, A. V. Chizmeshya, J. Kouvetakis, and J. Menéndez (Arizona State University)

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F. Gencarelli, B. Vincent (imec), J. Demeulemeester, A. Vantomme (KU Leuven), A. Moussa, A. Franquet, A. Kumar, H. Bender, J. Meersschaut, W. Vandervorst, R. Loo, M. Caymax (imec), K. Temst (KU Leuven), and M. Heyns (imec)

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